

SnapLED

PRELIMINARY SPEC



Features:

- •HIGH LUMINANCE OUTPUT.
- •DESIGN FOR HIGH CURRENT OPERATION.
- SOLDERLESS MOUNTING TECHNIQUE.
- •LOW POWER CONSUMPTION.
- •LOW THERMAL RESISTANCE.
- •LOW PROFILE.

•PACKAGED IN TUBES FOR USE WITH AUTOMATIC INSERTION EQUIPMENT. •RoHS COMPLIANT.



ATTENTION OBSERVE PRECAUTIONS FOR HANDLING ELECTROSTATIC DISCHARGE SENSITIVE DEVICES

Benefits:

- *Rugged Lighting Products.
- *Electricity savings.
- *Maintenance savings.
- *Environmental Conformance.

Typical Applications:

*Automotive Exterior Lighting. *Solid State Lighting and Signaling.

Absolute Maximum Ratings (TA=25°C)		DG (AlInGaN)	Unit
Reverse Voltage	VR	5	V
Forward Current	IF	30	mA
Power Dissipation	Рт	126	mW
Operating Temperature	ТА	$-40 \sim +85$	•0
Storage Temperature	Tstg	$-55 \sim +85$	C
Electrostatic Discharge Threshold (HBM)	450	V



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
- 3. Specifications are subject to change without notice.



Operating Characteristic (TA=25°C)	8	DG (AlInGaN)	Unit
Forward Voltage (Typ.) (IF=30mA)	$\mathbf{V}\mathbf{F}$	3.4	v
Forward Voltage (Max.) (IF=30mA)	$\mathbf{V}\mathbf{F}$	4.2	v
Reverse Current (Max.) (VR=5V)	IR	10	uA
Wavelength of Peak Emission (Typ.) (IF=30mA)	λΡ	515	nm
Wavelength of Dominant Emission (Typ.) (IF=30mA)	λ D	525	nm
Spectral Line Full Width At Half-Maximum (Typ.) (IF=30mA)	Δλ	30	nm
Capacitance (Typ.) (VF=0V, f=1MHz)	С	45	pF
Thermal Resistance (Typ.)	Rθj-pin	150	°C/W

1. The dominant wavelength is derived from the CIE Chromaticity Diagram and represents the perceived color of the device.

Published Date : JUN 05,2008

Checked : B.L.LIU

V3



Part Number: XSDG120W

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